



P. Pourrouquet, V. Traisnel and N. Chatry (TRAD) G. Rolland and R. Ecoffet (CNES)



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- Introduction of high Z metals in CMOS technology evolution (memories, FPGA...)
- Noticeable effects (SEE) on electronic parts:
  - R&T CNES 2015 for studying components with Copper back-end
- Presence of recoil atoms with LET > 15 MeV.cm<sup>2</sup>/mg in sensitive layer?
  - NASA's Guide Test Proton
    - Proton SEE testing is required when: a device has an heavy ion LET<sub>th</sub> < 37 MeV\*cm2/mg where no events occur at a test fluence of 1x10<sup>7</sup> particles/cm2, and, mission proton exposure is significant
  - Cu LET > 15 MeV.cm<sup>2</sup>/mg for Energy > 9 MeV
  - W LET > 15 MeV.cm<sup>2</sup>/mg for Energy > 0.2 MeV







- Theoretical study
- 3D model description
- Results
- Conclusions
- Perspectives





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## Recoil atom creation areas

- Metallization (Cu)
- At the Via level between the first metal layer and the sensitive area
- Silicide/nitride layer
  (10 nm)
- Creation energy and range
  - => Study of the 4 metal layers

# Definition of representative3D models for the study

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Recoil atoms can reach the sensitive area from all the 4 metal layers





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CIS Front-end

#### **Metal layers**



Figure 2 : First metal layer

#### Metal 0.2 μm Oxide 0.8 μm (\*) Silicon 1 μm

Figure 3 : Second metal layer

(\*) The oxide layer replaces the different layers between the second metal layer and the silicon sensitive area.

## Metal1 + Via in Copper

#### Metal 0.15 µm Metal 0.5 µm Silicon 1 µm

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Figure 6 : First metal layer and via just above the sensitive layer





Metal1 + Via in Copper



« Forbidden area » to prevent particles from entering through the lateral or the bottom sides

**Cross section view** 







## Simulation of a proton irradiation beam

## 

| 4 |  |
|---|--|

## Mono-energetic protons with a normal incidence

- Sampling energies from highest available (480 MeV) to 0 MeV
- For each component the simulations are repeated for all the 6 models

- Modification of TRADCARE tool to compute an LET Spectrum in the Silicon sensitive volume instead of carried deposition
- For each calculation, creation of an LET spectrum for each ion species depending on their atomic mass (Z)

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 Useful to establish the list of ions reaching the sensitive volume







Atome de cuivre

Atome de tungstène

Entrée en zone active

## H9A Component

Cap et Passivation 2850 → 3380 nm

SiO<sub>2</sub> 630 nm

SiO, 400 nm

SiO<sub>2</sub> 400 nm

SiO<sub>2</sub> 570 nm

\_\_\_\_1μm

M4 900 nm

M3 350 nm

M2 350 nm

M1 570 nm

Silicon

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H9A Back-end 4.17 µm



Metal 1-Via + W 480 MeV

#### LET (MeV.cm<sup>2</sup>.mg-1)

| Model                | Number of<br>tracked<br>protons | Proton lowest energy to<br>obtain LET > 15<br>MeV.cm <sup>2</sup> .mg <sup>-1</sup> | Highest LET obtained<br>for 480 MeV protons<br>(MeV.cm <sup>2</sup> .mg <sup>-1</sup> ) | Z max   |
|----------------------|---------------------------------|---|---|---------|
| Metal 2              | 1.00E+08                        | / (*)   | 15  | 14 (Si) |
| Metal 1              | 1.00E+08                        | 355 MeV   | 26  | 28 (Ni) |
| Metal 1+             |                                 |   |   |         |
| Via                  | 1.00E+08                        | 105 MeV   | 25  | 30 (Zn) |
| Metal 1 +<br>Via + W | 1.00E+08                        | 55 MeV  | 26  | 75 (Re) |

Table 1 : Result summary for proton normal beam on H9A component







SiO, et SiN 800 nm

## **CIS Component**

4.43 µm



Métal 1 + Via + W 480 MeV



50 MeV

50 MeV

Tableau 3 : Result summary for proton normal beam on CIS component

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Via

Metal 1+

Via + W

1.00E+08

1.00E+08

26

31

29 (Cu)

28 (Ni)

29 (Cu)

29 (Cu)

30 (Zn)

75 (Re)



#### Recoil atoms creation areas:

- All the metal layers
- Highest LET for particles created in the via and the silicide/nitride layer: 31 MeV.cm<sup>2</sup>/mg<sup>-1</sup>
- 50 MeV protons are energetic enough to have atoms with a LET higher than 15 MeV.cm<sup>2</sup>/mg<sup>-1</sup> present in the sensitive layer

#### • Creation energy :

- Necessary proton energy decreases when the creation areas are closer to the sensitive layer:
  - More than 300 MeV for layers above Metal2
  - 140 MeV for Metal1 layer
  - 50 MeV for the Via et silicide/nitride

#### Processes creating the recoil atoms

- Fragmentation (Z < Z<sub>target</sub>)
- Recoil (Z = Z<sub>target</sub>)
- Fusion (Z = Ztarget + 1)



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#### Qualitative and not quantitative study

- Hypotheses for the silicide/nitride composition
- Hypotheses for the metal layer and via area
- Sensitive layer thickness fixed to 1 μm
- Passivation layers not considered
- => Worst case study for LET calculation and not possible to conclude on the actual probabilities of high LET atom creation

 Next year study will consider the quantitative aspect considering more realistic cases:

- More realistic component model definition,
- Proton environment: real spectrum



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## Thank you for your attention





